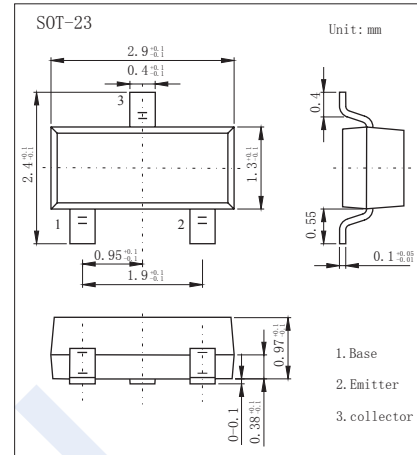


PNP Transistors

2SA1839-HF

■ Features

- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Low ON resistance.
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-15	V
Collector - Emitter Voltage	V _{CEO}	-10	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-100	mA
Collector Current - Pulse	I _{CP}	-200	
Base Current	I _B	-20	
Collector Power Dissipation	P _C	250	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E =0	-15			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} =∞	-10			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -12 V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA, I _B =-1mA		-0.04	-0.15	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-10mA, I _B =-1mA		-0.82	-1.1	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -5mA	200		600	
On Resistance	R _{on}	I _B = -3mA, f=1MHz		3		Ω
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		0.9		pF
Transition frequency	f _T	V _{CE} = - 5 V, I _C = -10mA		600		MHz

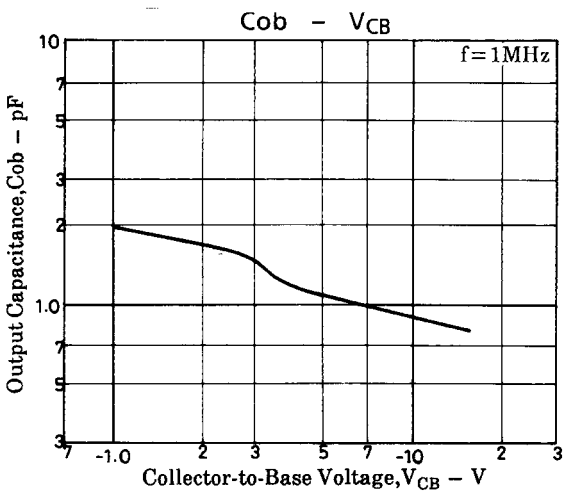
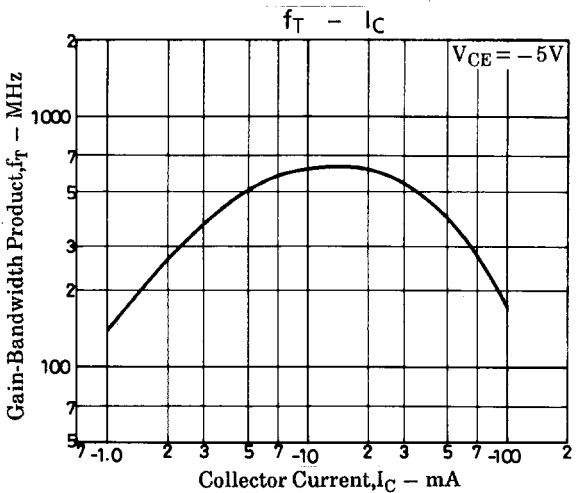
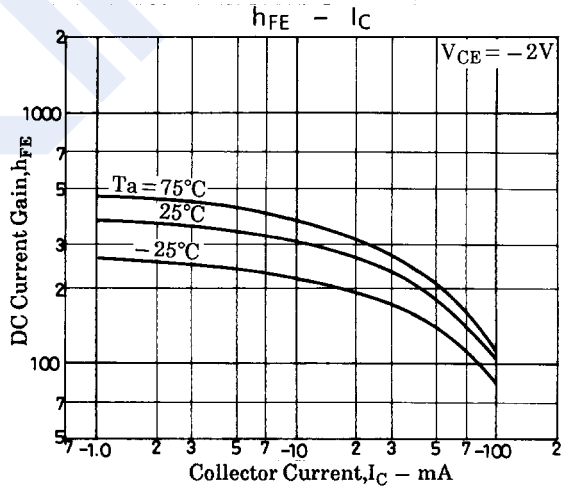
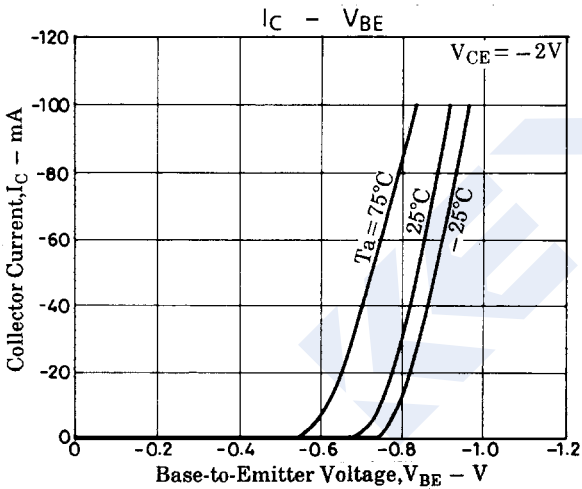
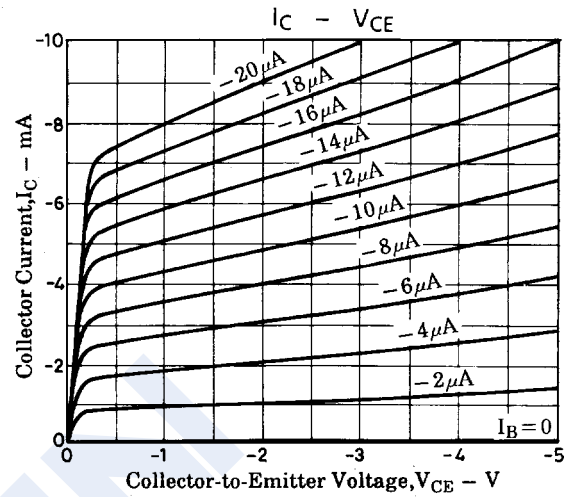
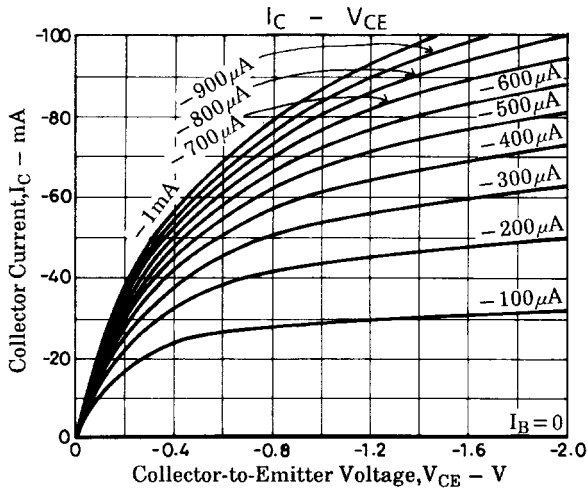
■ Marking

Marking	LS F
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PNP Transistors

2SA1839-HF

■ Typical Characteristics



PNP Transistors

2SA1839-HF

■ Typical Characteristics

